What we claim is,

1. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

(11-20) and (1-100) sides; and

a longer slanting edge (L) and a shorter slanting edge (S) formed at two obversely-clockwise neighboring corners on a side opposite to the (11-20) side as a reference side.

2. The obverse/reverse discriminative rectangular nitride semiconductor wafer according to claim 1, wherein lengths of the longer slanting edge (L) and the shorter slanting edge (S) satisfy inequalities $S<L$, $K/40 \leqq L \leqq K/12$ and $K/40 \leqq S \leqq K/16$, where K is a sum of lengths of four sides of the rectangular wafer.

3. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

(11-20) and (1-100) sides; and

a longer slanting edge (L) and a shorter slanting edge (S) formed at two obversely-clockwise neighboring corners on a side opposite to the (1-100) side as a reference side.

4. The obverse/reverse discriminative rectangular nitride semiconductor wafer according to claim 3, wherein lengths of the longer slanting edge (L) and the shorter slanting edge (S) satisfy inequalities $S<L$, $K/40 \leqq L \leqq K/12$ and $K/40 \leqq S \leqq K/16$, where K is a sum of lengths of four sides of the rectangular wafer.

5. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

(11-20) and (1-100) sides; and

an asymmetric slanting edge formed at an obverse-counterclockwise corner of a

(-1-120) side opposite to the (11-20) side as a reference side,

the asymmetric slanting edge inclining to an obverse-counterclockwise neighboring side at an angle Θ between 5degrees and 40degrees ($5^\circ \leqq \Theta \leqq 40^\circ$) and having a length between K/40 and K/16, where K is a sum of lengths of four sides of the rectangular wafer.

6. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

(11-20) and (1-100) sides; and

an asymmetric slanting edge formed at an obverse-counterclockwise corner of a (-1100) side opposite to the (1-100) side as a reference side,

the asymmetric slanting edge inclining to an obverse-counterclockwise neighboring side at an angle Θ between 5degrees and 40degrees ($5^\circ \leqq \Theta \leqq 40^\circ$) and having a length between K/40 and K/16, where K is a sum of lengths of four sides of the rectangular wafer.

7. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1); and

(11-20) and (1-100) sides,

wherein the sides are bevelled asymmetrically for an obverse and a reverse and an obverse bevelling width (g) is smaller than a reverse bevelling width (h).

8. The obverse/reverse discriminative rectangular nitride semiconductor wafer according to claim 7, wherein the obverse bevelling width (g) and the reverse bevelling with (h) satisfy inequalities of $g < h$, $100\,\mu m \leqq g \leqq 400\,\mu m$ and $300\,\mu m \leqq h \leqq 1000\,\mu m$.

9. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

(11-20) and (1-100) sides; and

characters written in normal posture on the obverse surface in parallel with the (11-20) side along a [1-100] direction by laser marking.

10. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

(11-20) and (1-100) sides; and

characters written in inverse posture on the obverse surface in parallel with the (11-20) side along a [1-100] direction by laser marking.

11. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

a reverse surface opposite to the obverse surface;

(11-20) and (1-100) sides; and

characters written in normal posture on the reverse surface in parallel with the (11-20) side in a [1-100] direction by laser marking.

12. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

a reverse surface opposite to the obverse surface;

(11-20) and (1-100) sides; and

characters written in inverse posture on the reverse surface in parallel with the (11-20) side in a [1-100] direction by laser marking.

13. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

(11-20) and (1-100) sides; and

characters written in normal posture on the obverse surface in parallel with the (1-100) side in a [11-20] direction by laser marking.

14. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

(11-20) and (1-100) sides; and

characters written in inverse posture on the obverse surface in parallel with (1-100) side in a [11-20] direction by laser marking.

15. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

a reverse surface opposite to the obverse surface;

(11-20) and (1-100) sides; and

characters written in normal posture on the reverse surface in a [11-20] direction in parallel with the (1-100) side by laser marking.

16. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

a reverse surface opposite to the obverse surface;

(11-20) and (1-100) sides; and

characters written in inverse posture on the reverse surface in a [11-20] direction in parallel with the (1-100) side by laser marking.